Patent Claims

1. A power semiconductor module comprising a plurality of semiconductor components situated on a substrate, wherein

- the substrate has a plurality of substrate regions and
- one or a plurality of connecting regions are situated between substrate regions, via which connecting regions the substrate regions are connected such that they can move relative to one another.

2. The power semiconductor module as claimed in claim 1, wherein

- the connecting regions are formed by recesses in the material of the substrate.

3. The power semiconductor module as claimed in claim 2, wherein

- the material recesses are slotted.

4. The power semiconductor module as claimed in claim 1, wherein

- the substrate is a ceramic.

5. The power semiconductor module as claimed in claim 2, wherein

- the substrate is a ceramic.

6. The power semiconductor module as claimed in claim 3, wherein

- the substrate is a ceramic.

7. The power semiconductor module as claimed in claim 1, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

8. The power semiconductor module as claimed in claim 2, wherein
- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

9. The power semiconductor module as claimed in claim 3, wherein
- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

10. The power semiconductor module as claimed in claim 4, wherein
- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

11. The power semiconductor module as claimed in claim 5, wherein
- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

12. The power semiconductor module as claimed in claim 6, wherein
- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

13. The power semiconductor module as claimed in claim 1, wherein
- the power semiconductor module has a housing, which, in the region between the substrate regions, has action points for a mechanical pressure application of the connecting regions, and
- the housing applies pressure to the individual substrate regions.